General Description

FSMOS® MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially designed to use in power supply systems with driving voltage of more than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

RoHS compliant

Applications

- Switched mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Inverter
- UPS

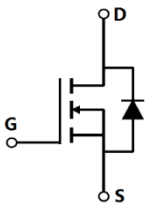
Key Performance Parameters

Parameter	Value	Unit
$V_{DS,\ min}$ @ $T_{j(max)}$	80	V
$I_{D,\ pulse}$	420	A
$R_{DS(ON),\ max}$ @ V_{GS}=10V	5	mΩ
Q_g	30	nC
PD	98	W

Marking Information

Product Name	Package	Marking
SFS08R05KNF	TO-263-2L	SFS08R05KN

Package & Pin information



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Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	80	V
Gate-source voltage	V_{GS}	±20	V
Continuous drain current[1], T_C=25 °C	I_D	105	A
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	420	A
Continuous diode forward current[1], T_C=25 °C	I_S	105	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	420	A
Power dissipation[3], T_C=25 °C	P_D	98	W
Single pulsed avalanche energy[5]	E_{AS}	109	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	1.27	°C/W
Thermal resistance, junction-ambient[4]	$R_{\theta JA}$	62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	80			V	V_{GS}=0 V, I_D=250 μA
Gate threshold voltage	$V_{GS(th)}$	2		4	V	V_{DS}=V_{GS}, I_D=250 μA
Drain-source on-state resistance	$R_{DS(ON)}$		4.3	5	mΩ	V_{GS}=10 V, I_D=50 A
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=20 V
				-100		V_{GS}=-20 V
Drain-source leakage current	I_{DSS}			1	μA	V_{DS}=80 V, V_{GS}=0 V
Gate resistance	R_G		2.2		Ω	f=1 MHz, Open drain

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Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		2057		pF	V_{GS}=0 V, V_{DS}=25 V, f=100 kHz
Output capacitance	C_{oss}		1342		pF	
Reverse transfer capacitance	C_{rss}		81		pF	
Turn-on delay time	$t_{d(on)}$		13		ns	V_{GS}=10 V, V_{DS}=40 V, R_G=2 Ω, I_D=40 A
Rise time	t_r		6		ns	
Turn-off delay time	$t_{d(off)}$		22		ns	
Fall time	t_f		7		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		30		nC	V_{GS}=10 V, V_{DS}=40 V, I_D=40 A
Gate-source charge	Q_{gs}		9		nC	
Gate-drain charge	Q_{gd}		7.5		nC	
Gate plateau voltage	$V_{plateau}$		4.5		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	I_S=50 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		26		ns	V_R=50 V, I_S=50 A, di/dt=400 A/μs
Reverse recovery charge	Q_{rr}		51		nC	
Peak reverse recovery current	I_{rrm}		3.6		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C
5) V_{DD}=50 V,V_{GS}=10 V, L=0.3 mH, starting T_j=25 °C.

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Electrical Characteristics Diagrams

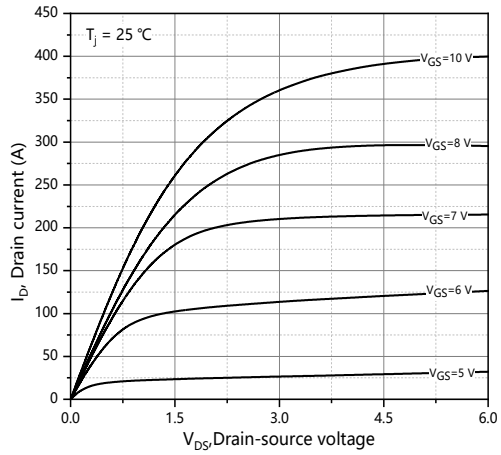

Figure 1. Typ. output characteristics

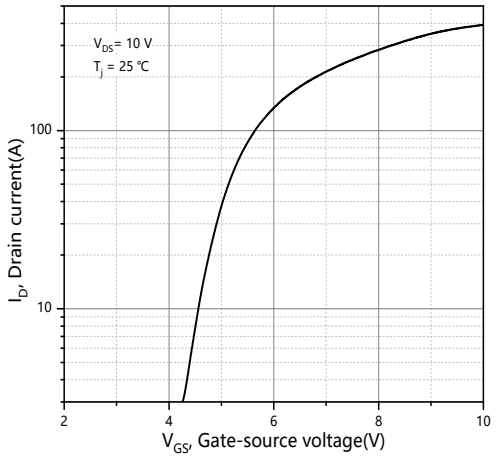

Figure 2. Typ. transfer characteristics

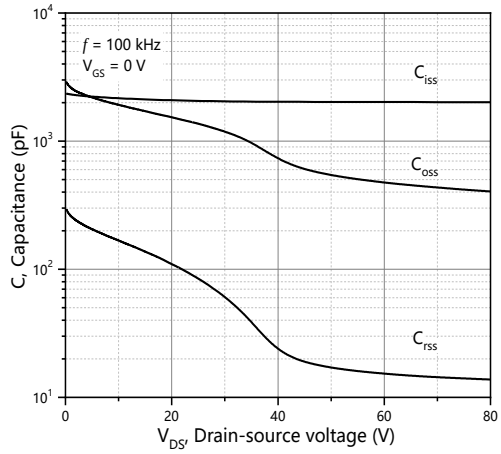

Figure 3. Typ. capacitances

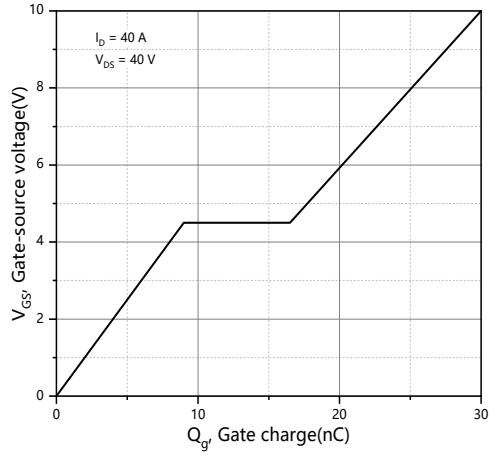

Figure 4. Typ. gate charge

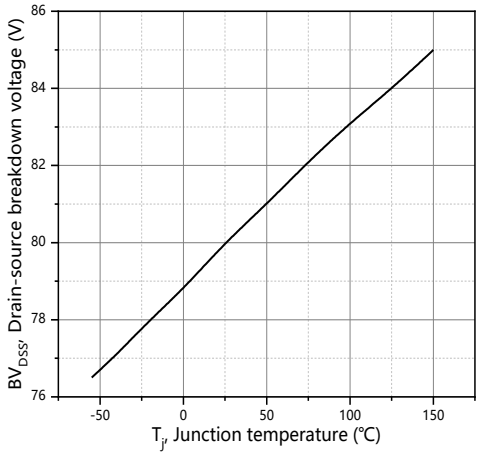

Figure 5. Drain-source breakdown voltage

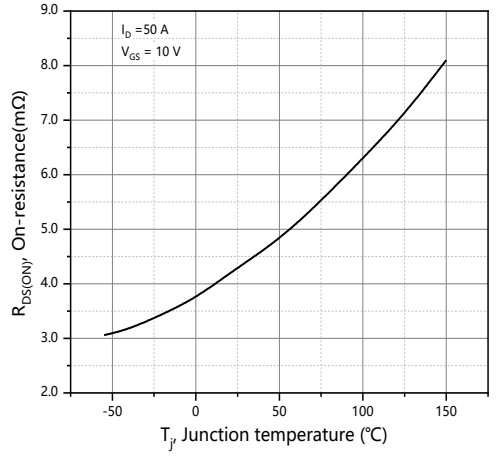

Figure 6. Drain-source on-state resistance

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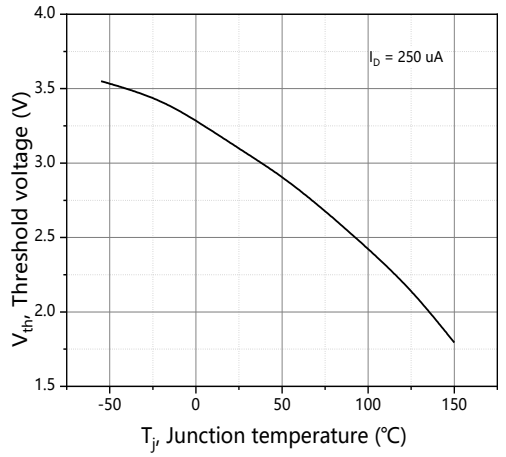


Figure 7. Threshold voltage

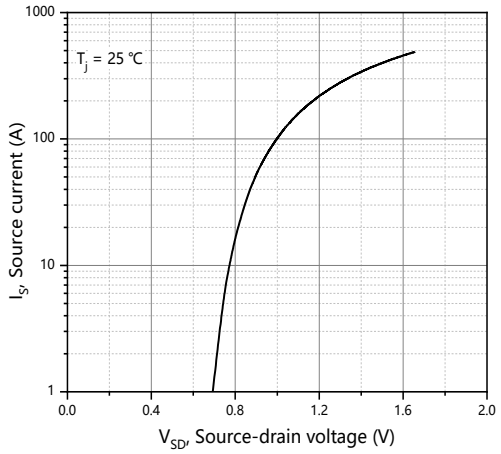


Figure 8. Forward characteristic of body diode

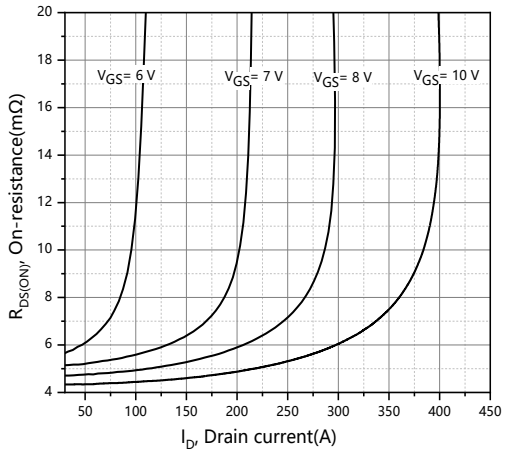


Figure 9. Drain-source on-state resistance

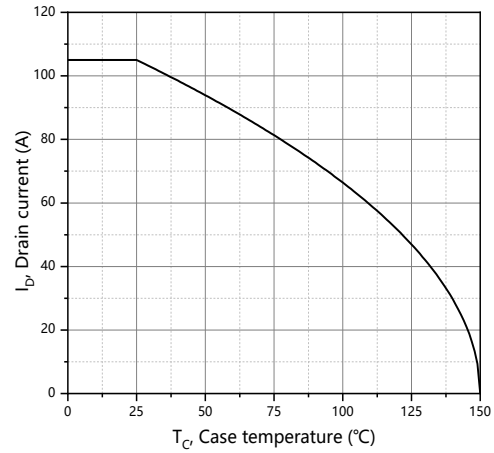


Figure 10. Drain current

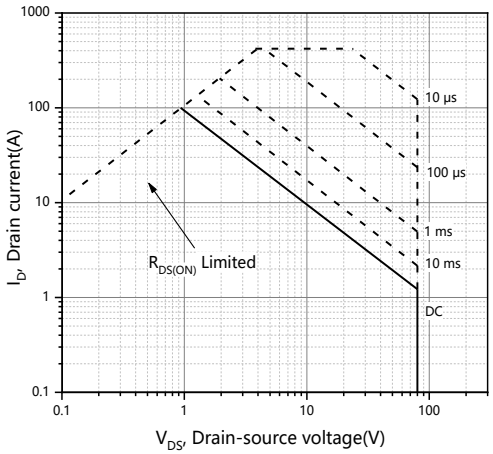


Figure 11. Safe operation area T_C=25 ℃

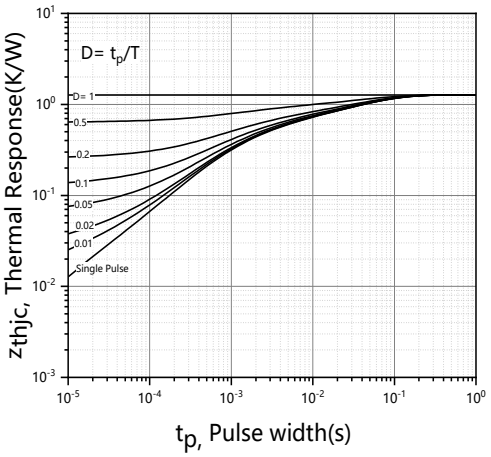


Figure 12. Max. transient thermal impedance

Test circuits and waveforms

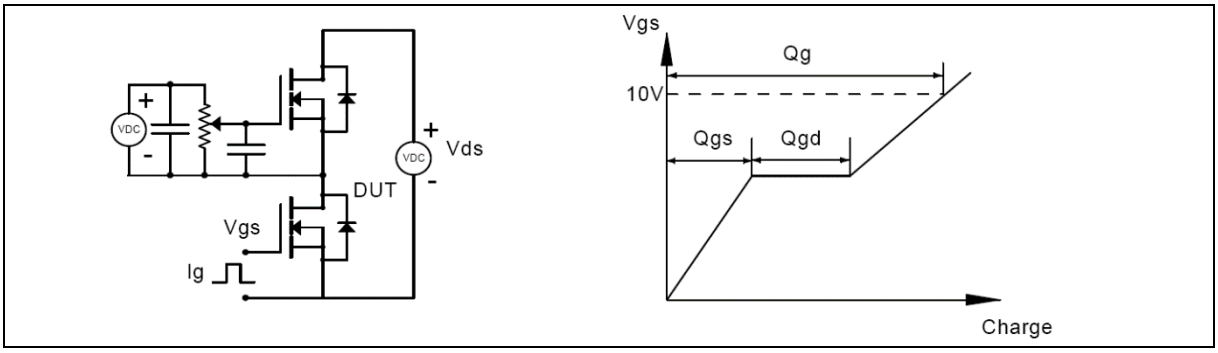


Figure 1. Gate charge test circuit & waveform

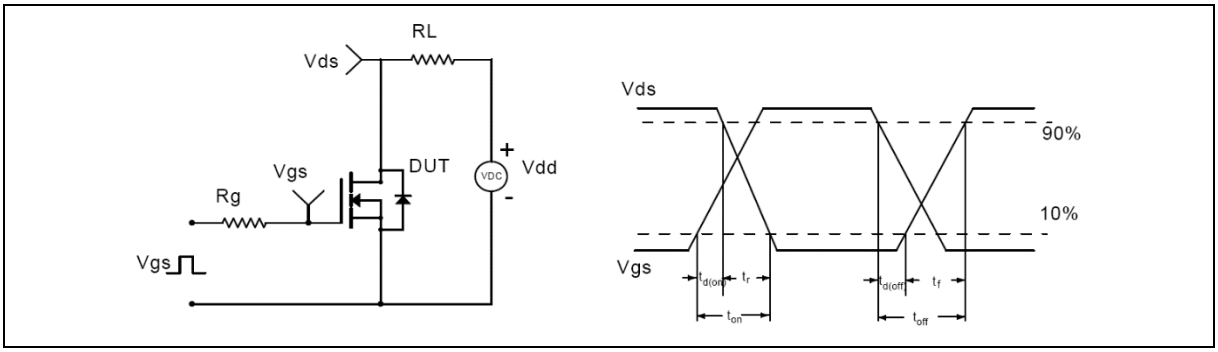


Figure 2. Switching time test circuit & waveforms

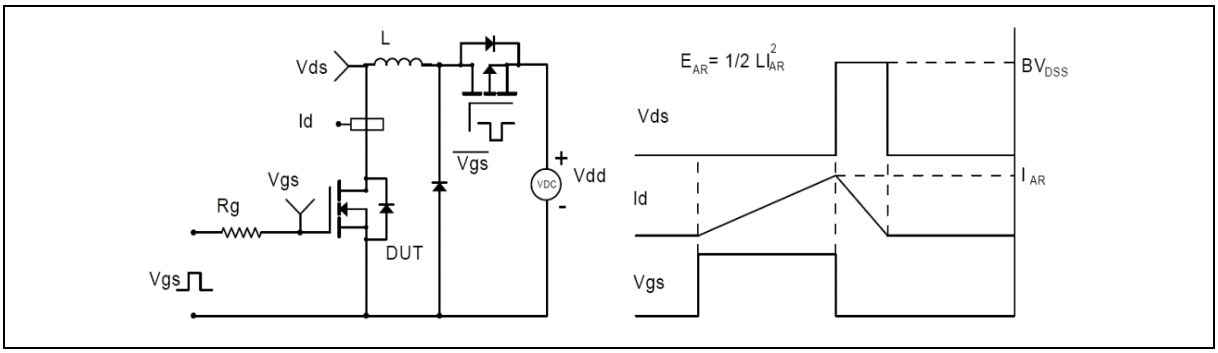


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

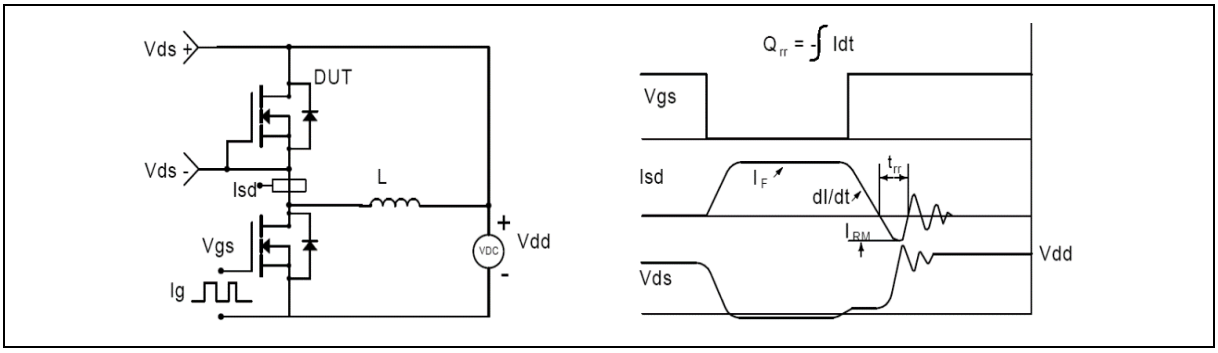
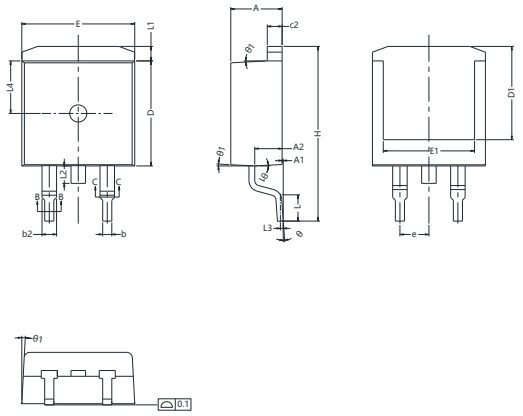


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.40	4.50	4.60
A1	0.00	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	——	0.89
b2	1.23	——	1.37
c	0.47	——	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	——	——
E	9.80	9.90	10.00
E1	7.80	——	——
e	2.54BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.30
L1	1.17	1.27	1.40
L2	——	——	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	——	8°
θ1	1°	3°	5°

Version : TO-263-2L-J package outline dimension

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Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO-263-2L-J	800	1	800	10	8000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFS08R05KNF	TO-263-2L	yes	yes	yes

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Revision History

Version	Revision History	Date
V1.0	Initial release	2025-04-25

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